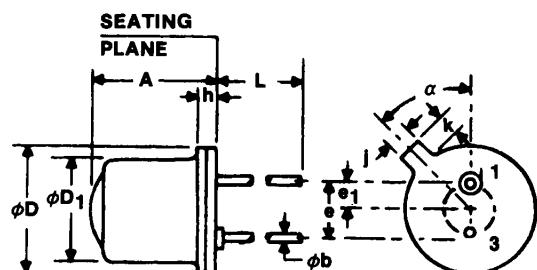




## GaAs INFRARED EMITTING DIODE

**CQX14, CQX16**

### PACKAGE DIMENSIONS



ST1332

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	.255		6.47		
phi b	.016	.021	.407	.533	
phi D	.209	.230	5.31	5.84	
phi D <sub>1</sub>	.180	.187	4.52	4.77	
e	.100 NOM.		2.54 NOM.		2
e <sub>1</sub>	.050 NOM.		1.27 NOM.		2
h	.030		.76		
j	.031	.044	.79	1.11	
k	.036	.046	.92	1.16	1
L	1.00		25.4		
alpha	45°	45°	45°	45°	3

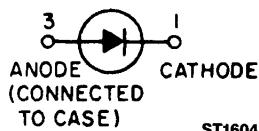
### DESCRIPTION

The CQX14/16 are 940nm LEDs in narrow angle, TO-46 packages.

### FEATURES

- Good optical to mechanical alignment
- Mechanically and wavelength matched to TO-18 phototransistor
- Hermetically sealed package
- High irradiance level
- European "Pro Electron" registered

### PACKAGE OUTLINE



ST1604

#### NOTES:

1. MEASURED FROM MAXIMUM DIAMETER OF DEVICE.
2. LEADS HAVING MAXIMUM DIAMETER .021" (.533mm)  
MEASURED IN GAUGING PLANE .054" + .001" - .000  
(137 + 025 - 000mm) BELOW THE REFERENCE  
PLANE OF THE DEVICE SHALL BE WITHIN .007"  
(.778mm) THEIR TRUE POSITION RELATIVE TO  
MAXIMUM WIDTH TAB.
3. FROM CENTERLINE TAB.



## GaAs INFRARED EMITTING DIODE

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Storage Temperature .....	.....	−65°C to +150°C
Operating Temperature .....	.....	−65°C to +125°C
Soldering:		
Lead Temperature (Iron) .....	.....	240°C for 5 sec. <sup>(3,4,5,6)</sup>
Lead Temperature (Flow) .....	.....	260°C for 10 sec. <sup>(3,4,6)</sup>
Continuous Forward Current .....	.....	100 mA
Forward Current (pw, 1 $\mu\text{s}$ ; 200 Hz) .....	.....	10 A
Reverse Voltage .....	.....	3 Volts
Power Dissipation ( $T_A = 25^\circ\text{C}$ ) .....	.....	170 mW <sup>(1)</sup>
Power Dissipation ( $T_c = 25^\circ\text{C}$ ) .....	.....	1.3 W <sup>(2)</sup>

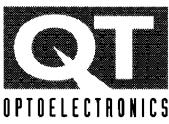
### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

(All measurements made under pulse conditions.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Forward Voltage	$V_F$	—	—	1.7	V	$I_F = 100 \text{ mA}$
Reverse Leakage Current	$I_R$	—	—	10	$\mu\text{A}$	$V_R = 3 \text{ V}$
Peak Emission Wavelength	$\lambda_P$	—	940	—	nm	$I_F = 100 \text{ mA}$
Emission Angle at $1/2$ Power	$\theta$	—	$\pm 8$	—	Degrees	
Total Power CQX14	$P_o$	5.4	—	—	mW	$I_F = 100 \text{ mA}^{(7)}$
Total Power CQX16	$P_o$	1.5	—	—	mW	$I_F = 100 \text{ mA}^{(7)}$
Rise Time 0-90% of output	$t_r$	—	1.0	—	$\mu\text{s}$	
Fall Time 100-10% of output	$t_f$	—	1.0	—	$\mu\text{s}$	

### NOTES

1. Derate power dissipation linearly 1.70mW/ $^\circ\text{C}$  above  $25^\circ\text{C}$  ambient.
2. Derate power dissipation linearly 13.0mW/ $^\circ\text{C}$  above  $25^\circ\text{C}$  case.
3. RMA flux is recommended.
4. Methanol or Isopropanol alcohols are recommended as cleaning agents.
5. Soldering iron tip  $1/16''$  (1.6 mm) minimum from housing.
6. As long as leads are not under any stress or spring tension.
7. Total power output,  $P_o$ , is the total power radiated by the device into a solid angle of  $2\pi$  steradians.



## GaAs INFRARED EMITTING DIODE

### TYPICAL CHARACTERISTICS

